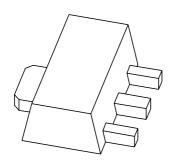
DISCRETE SEMICONDUCTORS

DATA SHEET



BZV49 seriesVoltage regulator diodes

Product specification Supersedes data of 1999 May 11 2005 Feb 03





Voltage regulator diodes

BZV49 series

FEATURES

• Total power dissipation: max. 1 W

• Tolerance series: approx. ±5%

• Working voltage range: nom. 2.4 to 75 V (E24 range)

 Non-repetitive peak reverse power dissipation: max. 40 W.

APPLICATIONS

· General regulation functions.

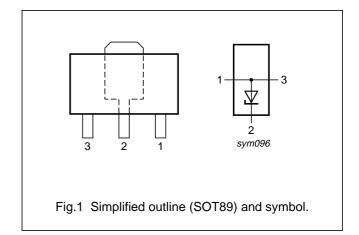
DESCRIPTION

Medium-power voltage regulator diodes in a SOT89 plastic SMD package.

The diodes are available in the normalized E24 approx. $\pm 5\%$ tolerance range. The series consists of 37 types with nominal working voltages from 2.4 to 75 V (BZV49-C2V4 to BZV49-C75).

PINNING

PIN	DESCRIPTION
1	anode
2	cathode
3	anode



ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
ITPE NUMBER	NAME	DESCRIPTION	VERSION
BZV49-C2V4 to BZV49-C75 note 1	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89

Note

1. The series consists of 37 types with nominal working voltages from 2.4 to 75 V (E24 range).

MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BZV49-C2V4	2Y4	BZV49-C6V2	6Y2	BZV49-C16	16Y	BZV49-C43	43Y
BZV49-C2V7	2Y7	BZV49-C6V8	6Y8	BZV49-C18	18Y	BZV49-C47	47Y
BZV49-C3V0	3Y0	BZV49-C7V5	7Y5	BZV49-C20	20Y	BZV49-C51	51Y
BZV49-C3Y3	3Y3	BZV49-C8V2	8Y2	BZV49-C22	22Y	BZV49-C56	56Y
BZV49-C3V6	3Y6	BZV49-C9V1	9Y1	BZV49-C24	24Y	BZV49-C62	62Y
BZV49-C3V9	3Y9	BZV49-C10	10Y	BZV49-C27	27Y	BZV49-C68	68Y
BZV49-C4V3	4Y3	BZV49-C11	11Y	BZV49-C30	30Y	BZV49-C75	75Y
BZV49-C4V7	4Y7	BZV49-C12	12Y	BZV49-C33	33Y	_	_
BZV49-C5V1	5Y1	BZV49-C13	13Y	BZV49-C36	36Y	_	_
BZV49-C5V6	5Y6	BZV49-C15	15Y	BZV49-C39	39Y	_	_

Voltage regulator diodes

BZV49 series

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _F	continuous forward current		_	250	mA
I _{ZSM}	non-repetitive peak reverse current	t_p = 100 μs; square wave; T_j = 25 °C prior to surge	see Table "Per type		
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	1	W
P _{ZSM}	non-repetitive peak reverse power dissipation	t_p = 100 μs; square wave; T_j = 25 °C prior to surge; see Fig.2	_	40	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on a ceramic substrate; area = 2.5 cm²; thickness = 0.7 mm.

ELECTRICAL CHARACTERISTICS

Total series

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	I _F = 50 mA; see Fig.3	1	V

Voltage regulator diodes

BZV49 series

Per type $T_j = 25$ °C unless otherwise specified.

BZV49- CXXX	WORKING VOLTAGE V _Z (V) at I _{Ztest}		DIFFERENTIAL RESISTANCE $r_{ m dif}\left(\Omega ight)$ at $I_{ m Ztest}$		TEMP. COEFF. S _Z (mV/K) at I _{Ztest} see Figs 4 and 5			TEST CURRENT I _{Ztest} (mA)	DIODE CAP. C_d (pF) at f = 1 MHz; at $V_R = 0$ V	REVERSE CURRENT at REVERSE VOLTAGE		NON-REPETITIVE PEAK REVERSE CURRENT $I_{ZSM} (A)$ at $t_p = 100 \mu s$;	
										I _R (μ A)	V _R	T _{amb} = 25 °C	
	MIN.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.		MAX.	MAX.	(V)	MAX.	
2V4	2.2	2.6	70	100	-3.5	-1.6	0	5	450	50	1.0	6.0	
2V7	2.5	2.9	75	100	-3.5	-2.0	0	5	450	20	1.0	6.0	
3V0	2.8	3.2	80	95	-3.5	-2.1	0	5	450	10	1.0	6.0	
3V3	3.1	3.5	85	95	-3.5	-2.4	0	5	450	5	1.0	6.0	
3V6	3.4	3.8	85	90	-3.5	-2.4	0	5	450	5	1.0	6.0	
3V9	3.7	4.1	85	90	-3.5	-2.5	0	5	450	3	1.0	6.0	
4V3	4.0	4.6	80	90	-3.5	-2.5	0	5	450	3	1.0	6.0	
4V7	4.4	5.0	50	80	-3.5	-1.4	+0.2	5	300	3	2.0	6.0	
5V1	4.8	5.4	40	60	-2.7	-0.8	+1.2	5	300	2	2.0	6.0	
5V6	5.2	6.0	15	40	-2.0	+1.2	+2.5	5	300	1	2.0	6.0	
6V2	5.8	6.6	6	10	0.4	2.3	3.7	5	200	3	4.0	6.0	
6V8	6.4	7.2	6	15	1.2	3.0	4.5	5	200	2	4.0	6.0	
7V5	7.0	7.9	6	15	2.5	4.0	5.3	5	150	1	5.0	4.0	
8V2	7.7	8.7	6	15	3.2	4.6	6.2	5	150	0.7	5.0	4.0	
9V1	8.5	9.6	6	15	3.8	5.5	7.0	5	150	0.5	6.0	3.0	
10	9.4	10.6	8	20	4.5	6.4	8.0	5	90	0.2	7.0	3.0	
11	10.4	11.6	10	20	5.4	7.4	9.0	5	85	0.1	8.0	2.5	
12	11.4	12.7	10	25	6.0	8.4	10.0	5	85	0.1	8.0	2.5	
13	12.4	14.1	10	30	7.0	9.4	11.0	5	80	0.1	8.0	2.5	
15	13.8	15.6	10	30	9.2	11.4	13.0	5	75	0.05	10.5	2.0	
16	15.3	17.1	10	40	10.4	12.4	14.0	5	75	0.05	11.2	1.5	
18	16.8	19.1	10	45	12.4	14.4	16.0	5	70	0.05	12.6	1.5	
20	18.8	21.2	15	55	14.4	16.4	18.0	5	60	0.05	14.0	1.5	
22	20.8	23.3	20	55	16.4	18.4	20.0	5	60	0.05	15.4	1.25	
24	22.8	25.6	25	70	18.4	20.4	22.0	5	55	0.05	16.8	1.25	

Product specification

BZV49- CXXX	VOL [*] V _Z	KING FAGE (V) Ztest	$ \begin{array}{c c} \textbf{DIFFERENTIAL} & \textbf{TEMP. COEFF.} \\ \textbf{RESISTANCE} & \textbf{S}_{\textbf{Z}} \ (\textbf{mV/K}) \\ \textbf{r}_{\textbf{dif}} \ (\Omega) & \textbf{at I}_{\textbf{Ztest}} \\ \textbf{at I}_{\textbf{Ztest}} & \textbf{see Figs 4 and 5} \end{array} $		TEST CURRENT I _{Ztest} (mA)	DIODE CAP. C_d (pF) at f = 1 MHz; at $V_R = 0$ V	REVER CURREI REVER VOLTA	NT at RSE	NON-REPETITIVE PEAK REVERSE CURRENT I _{ZSM} (A) at t _p = 100 μs;			
									I _R (μ A)	V _R	T _{amb} = 25 °C	
	MIN.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.		MAX.	MAX.	(V)	MAX.
27	25.1	28.9	25	80	21.4	23.4	25.3	2	50	0.05	18.9	1.0
30	28.0	32.0	30	80	24.4	26.6	29.4	2	50	0.05	21.0	1.0
33	31.0	35.0	35	80	27.4	29.7	33.4	2	45	0.05	23.1	0.9
36	34.0	38.0	35	90	30.4	33.0	37.4	2	45	0.05	25.2	0.8
39	37.0	41.0	40	130	33.4	36.4	41.2	2	45	0.05	27.3	0.7
43	40.0	46.0	45	150	37.6	41.2	46.6	2	40	0.05	30.1	0.6
47	44.0	50.0	50	170	42.0	46.1	51.8	2	40	0.05	32.9	0.5
51	48.0	54.0	60	180	46.6	51.0	57.2	2	40	0.05	35.7	0.4
56	52.0	60.0	70	200	52.2	57.0	63.8	2	40	0.05	39.2	0.3
62	58.0	66.0	80	215	58.8	64.4	71.6	2	35	0.05	43.4	0.3
68	64.0	72.0	90	240	65.6	71.7	79.8	2	35	0.05	47.6	0.25
75	70.0	79.0	95	255	73.4	80.2	88.6	2	35	0.05	52.5	0.2

Voltage regulator diodes

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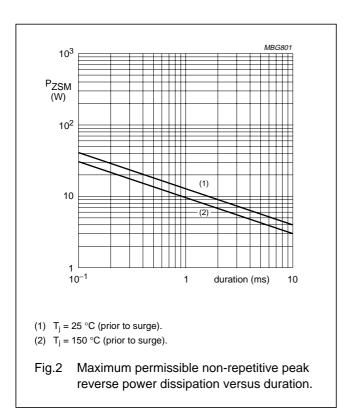
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-tp)}	thermal resistance from junction to tie-point		15	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	125	K/W

Note

1. Device mounted on a ceramic substrate; area = 2.5 cm²; thickness = 0.7 mm.

GRAPHICAL DATA



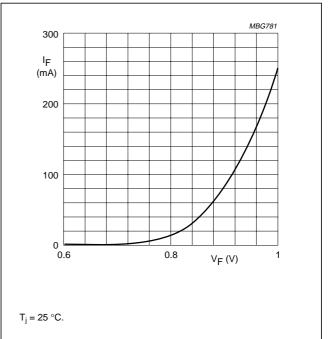
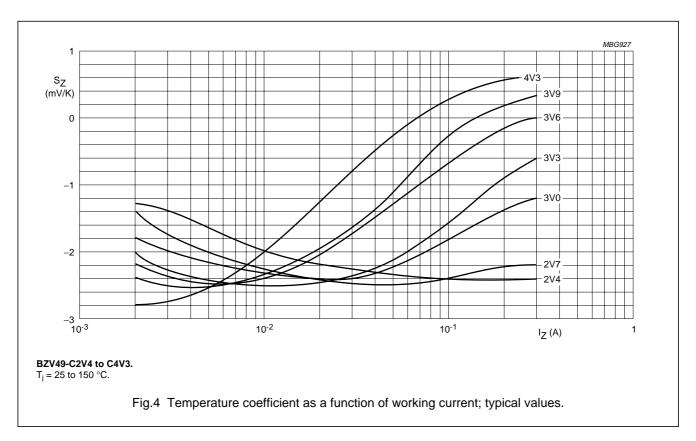
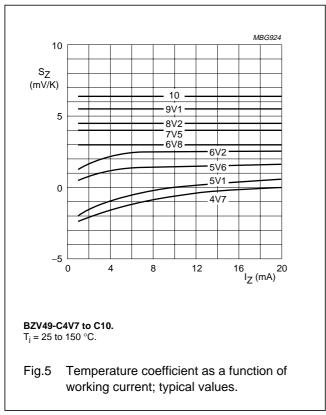


Fig.3 Forward current as a function of forward voltage; typical values.

Voltage regulator diodes

BZV49 series





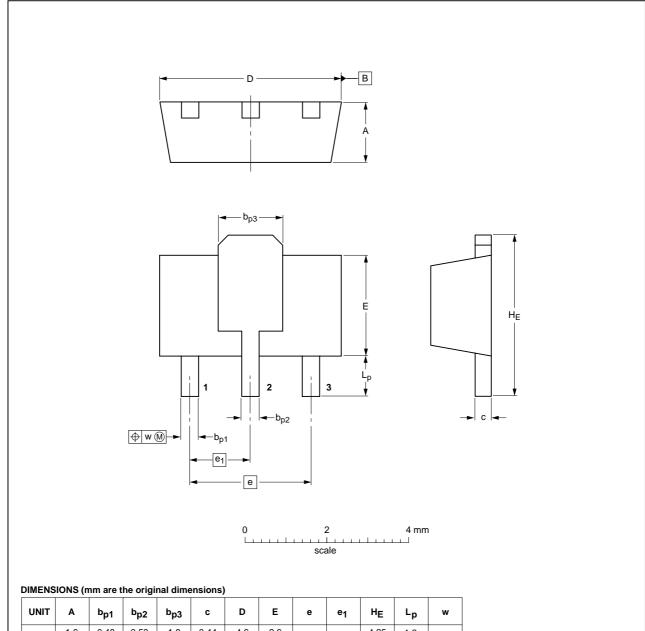
Voltage regulator diodes

BZV49 series

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



UNI	Α	b _{p1}	b _{p2}	b _{p3}	С	D	E	е	e ₁	HE	Lp	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE		EUROPEAN	ISSUE DATE				
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT89		TO-243	SC-62			99-09-13 04-08-03	

2005 Feb 03 8

Voltage regulator diodes

BZV49 series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
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